## Claims

What is claimed:

1. A method of making a semiconductor device, comprising:

providing a first semiconductor die;

forming a first inductor over the first semiconductor die;

forming a second inductor over the first inductor and aligned with the first inductor;

forming an insulating layer over the first semiconductor die and the first and second inductors; and

forming a conductive bridge over the insulating layer and electrically connected between the second inductor and the first semiconductor die.

2. The method of claim 1, further including:

providing a second semiconductor die; and

forming a conductive layer between the first and second semiconductor die.

3. The method of claim 1, further including forming a capacitor over the first semiconductor die.

~~3~~4. The method of claim 1, wherein the insulating layer has a first thickness outside a footprint of the first semiconductor die and a second thickness greater than the first thickness over a footprint of the first semiconductor die.

5. The method of claim 1, wherein a thickness of the insulating layer ranges between 5 and 25 micrometers.

6. The method of claim 1, further including forming an encapsulant over the first semiconductor die.

~~4~~7. A method of making a semiconductor device, comprising:

providing a first semiconductor die;

forming a first conductive layer ~~inductor~~ over the first semiconductor die; ~~and~~

~~forming a second inductor over the first inductor and aligned with the first inductor~~

forming an insulating layer over the first conductive layer; and

forming a second conductive layer over the insulating layer and first conductive layer to form an inductor and a portion of a capacitor.

~~5~~8. The method of claim ~~4~~7, wherein a portion of the second conductive layer extends outside a footprint of the capacitor~~further including:~~

~~forming an insulating layer over the first semiconductor die and the first and second inductors; and~~

~~forming a conductive bridge over the insulating layer and electrically connected between the second inductor and the first semiconductor die~~.

~~6~~9. The method of claim ~~5~~7, wherein the insulating layer has a first thickness outside a footprint of the first semiconductor die and a second thickness greater than the first thickness over a footprint of the first semiconductor die.

~~7~~10. The method of claim ~~4~~7, further including:

providing a second semiconductor die; and

forming a third conductive layer between the first and second semiconductor die.

11. The method of claim 7, wherein a portion of the second conductive layer extends vertically through an opening in the insulating layer to contact the first conductive layer.

12. The method of claim 7, wherein a thickness of the insulating layer ranges between 5 and 25 micrometers.

13. The method of claim 7, further including forming an encapsulant over the first semiconductor die.

14. A method of making a semiconductor device, comprising:

providing a first semiconductor die;

forming a plurality of integrated passive devices (IPDs) over the first semiconductor die;

forming an insulating layer over the first semiconductor die and the IPDs; and

forming a conductive bridge over the insulating layer and electrically connected between the IPDs and the first semiconductor die.

15. The method of claim 14, wherein forming the IPDs further includes:

forming a first inductor over the first semiconductor die; and

forming a second inductor over the first inductor and aligned with the first inductor.

16. The method of claim 14, further including:

providing a second semiconductor die; and

forming a conductive layer between the first and second semiconductor die.

17. The method of claim 14, further including forming a capacitor over the first semiconductor die.

18. The method of claim 14, wherein the insulating layer has a first thickness outside a footprint of the first semiconductor die and a second thickness greater than the first thickness over a footprint of the first semiconductor die.

19. The method of claim 14, wherein a thickness of the insulating layer ranges between 5 and 25 micrometers.

20. The method of claim 14, further including forming an encapsulant over the first semiconductor die.

~~8~~21. A semiconductor device, comprising:

a first semiconductor die;

a first inductor formed over the first semiconductor die;

a second inductor formed over the first inductor and aligned with the first inductor;

an insulating layer formed over the first semiconductor die and the first and second inductors; and

a conductive bridge formed over the insulating layer and electrically connected between the second inductor and the first semiconductor die.

~~9~~22. The semiconductor device of claim ~~8~~21, further including:

a second semiconductor die; and

a conductive layer formed between the first and second semiconductor die.

23. The semiconductor device of claim 21, further including:

a capacitor formed over the first semiconductor die.

~~10~~24. The semiconductor device of claim ~~8~~21, wherein the insulating layer has a first thickness outside a footprint of the first semiconductor die and a second thickness greater than the first thickness over a footprint of the first semiconductor die.

25. The semiconductor device of claim 21, wherein a thickness of the insulating layer ranges between 5 and 25 micrometers.

26. A semiconductor device, comprising:

a first semiconductor die;

a first inductor formed over the first semiconductor die including a portion directly contacting the semiconductor die; and

a second inductor formed over the first inductor to align with the first inductor.

27. The semiconductor device of claim 26, further including:

a second semiconductor die disposed over the first semiconductor die; and

a conductive layer formed between the first and second semiconductor die.

28. The semiconductor device of claim 26, further including:
a capacitor formed over the first semiconductor die.

29. The semiconductor device of claim 26, further including an insulating layer formed over the first semiconductor die.

30. The semiconductor device of claim 29, wherein a thickness of the insulating layer ranges between 5 and 25 micrometers.